

AMENDMENTS TO THE SPECIFICATION

1. Please substitute the paragraph 0022 on page 6 with the following paragraph:

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Please refer to Fig. 8 of a schematic view of forming a solder structure and performing a laser repair process for memory device on a semiconductor wafer according to a second embodiment of the present invention. In
10 this embodiment of the present invention, after forming the first dielectric layer 82 and the contact hole on the surface of the semiconductor wafer 80, the UBM process can be directly performed to form a metal layer 84 on the surface of the contact hole by sputtering.
15 Therefore, the process of forming the second dielectric layer 52 in the first embodiment of the present invention is omitted. After forming the metal layer 84, the following processes, just like the first embodiment of the present invention, comprise forming a solder
20 bump 86 on the metal layer 84 corresponding to the contact hole, performing a circuit probing process through the solder bump 86, and performing a laser repair process to cut off portions of the fuses 88. Finally, the semiconductor wafer 80 is placed on a packaging board
25 (not shown) and connected with the packaging board by performing a thermal treatment.